

Supporting Information

Hierarchical Carbon@Ni₃S₂@MoS₂ Double Core-Shell Nanorods for High-Performance Supercapacitors

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Table S1. Specific capacitance (F g⁻¹) at different current densities.

Samples	2 Ag ⁻¹	4 Ag ⁻¹	8 Ag ⁻¹	10 Ag ⁻¹	15 Ag ⁻¹	20 Ag ⁻¹	30 Ag ⁻¹	40 Ag ⁻¹	Retention
C@NM-300	633	582	520	487.5	446.25	405	352.5	320	50.55%
C@NM-500	1013	1000	886	865	776.25	695	645	550	54.27%
C@NM-700	1544	1500	1404	1388	1327	1280	1192	1170	75.97%
C@NM-900	1300	1270	1250	1220	1170	1121	1050.8	1005	77.31%

Note 1: “Retention” refers to the capacity at 40 A/g as compared with that at 2 A/g.

Table S2. Comparison of electrochemical performance of our C@Ni₃S₂@MoS₂ nanorods with the recently reported Ni₃S₂- and MoS₂-based hybrid materials

Materials	Capacitance (F/g)	Rate Performance	Capacitance retention	Reference
CNT@Ni ₃ S ₂	514 (4 A/g)	70.4% (13.3/4)	88% (5.3A/g, 1500)	1
Ni ₃ S ₂ /rGO	1015.6 (1 A/g)	87.9% (10/1)	85% (10 A/g, 1000)	2
NiCo ₂ O ₄ @Ni ₃ S ₂	1601 (2 A/g)	68.9% (20/2)	83.7% (4 A/g, 2000)	3
Ni@rGO– Ni ₃ S ₂	987.8 (1.5 A/g)	54.3% (20/1.5)	97.9% (12 A/g, 3000)	4
ZnO@Ni ₃ S ₂ array	1529 (2 A/g)	80.4% (20/2)	42% (10 A/g, 2000)	5
Ni ₃ S ₂ @Ni(OH) ₂ /3DGN	1037.5 (5.1 A/g)	38.4% (19.8/5.1)	99.1% (5.9 A/g, 2000)	6
Ni ₃ S ₄ @MoS ₂	1440.9 (2 A/g)	55.56% (20/2)	90.7%(10 A/g, 3000)	7
C@Ni₃S₂@MoS₂	1544 (2A/g)	82.9% (20/2)	92.8% (20 A/g, 2000)	Our work

Note 2: “514 (4 A/g)” means the capacitance is 514 F/g at 4 A/g,

“70.4% (13.3/4)” refers to the capacitance at 13.3 A/g is 70.4% of that at 4 A/g,

“88% (5.3A/g, 1500)”represents that the capacitance retention is 88% after 1500 cycles at 5.3 A/g.

Table S3. Weight ratio of C, S, N and H from combustion analysis.

Samples	C (%)	S (%)	N (%)	H (%)
C@NM-300	11.01	14.03	5.14	2.09
C@NM-500	12.89	15.99	5.03	1.86
C@NM-700	16.72	13.22	5.00	1.52
C@NM-900	15.75	11.77	5.19	2.13

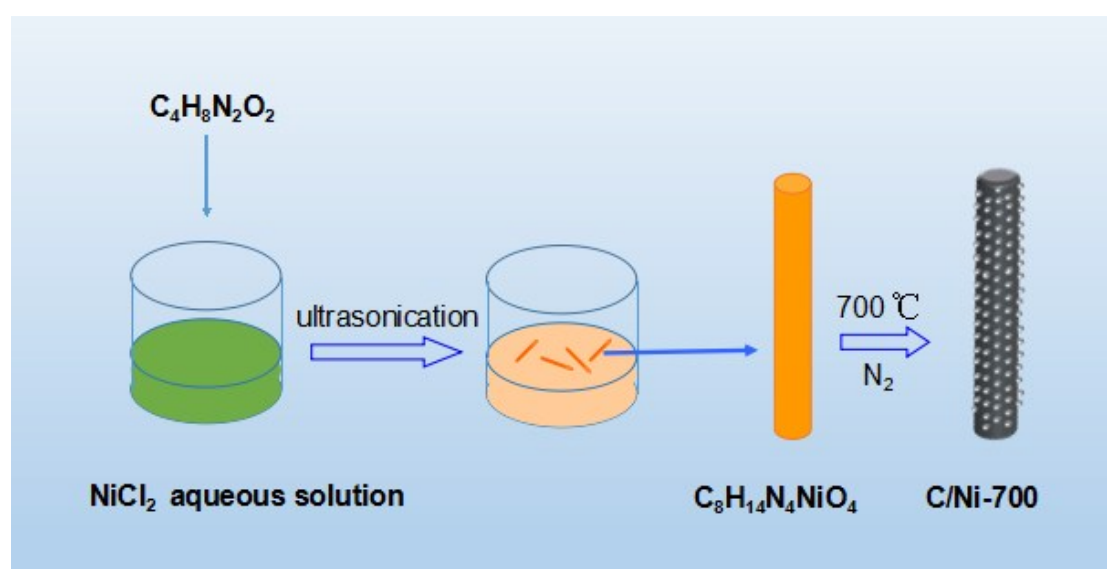


Fig. S1 Schematic illustration to show the formation of the C/Ni-700 nanorods.

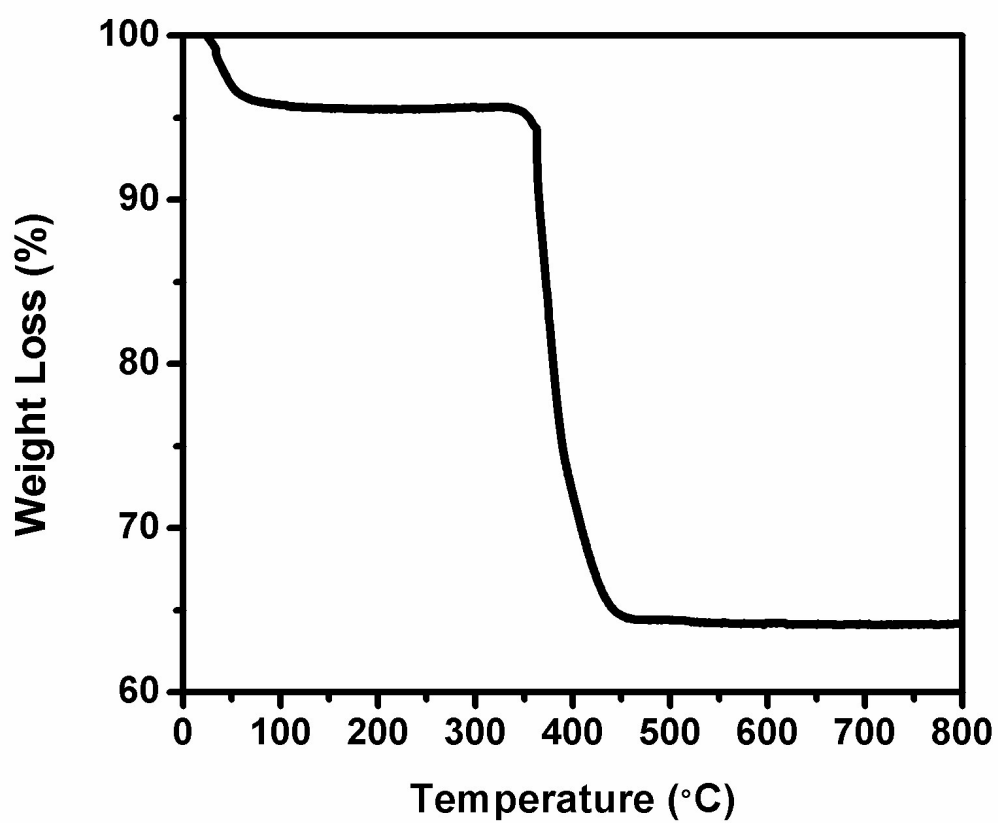


Fig. S2 Thermogravimetric curve of C/Ni-700 nanorods.

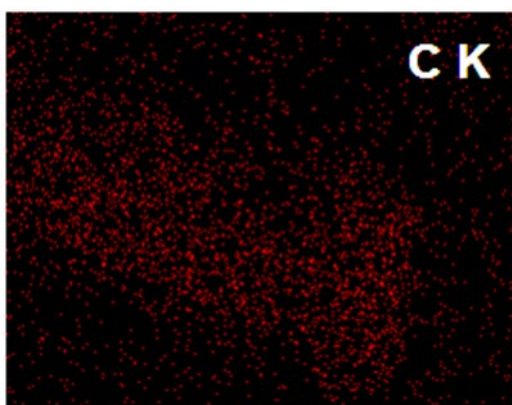


Fig. S3 EDX elemental mapping image for carbon.

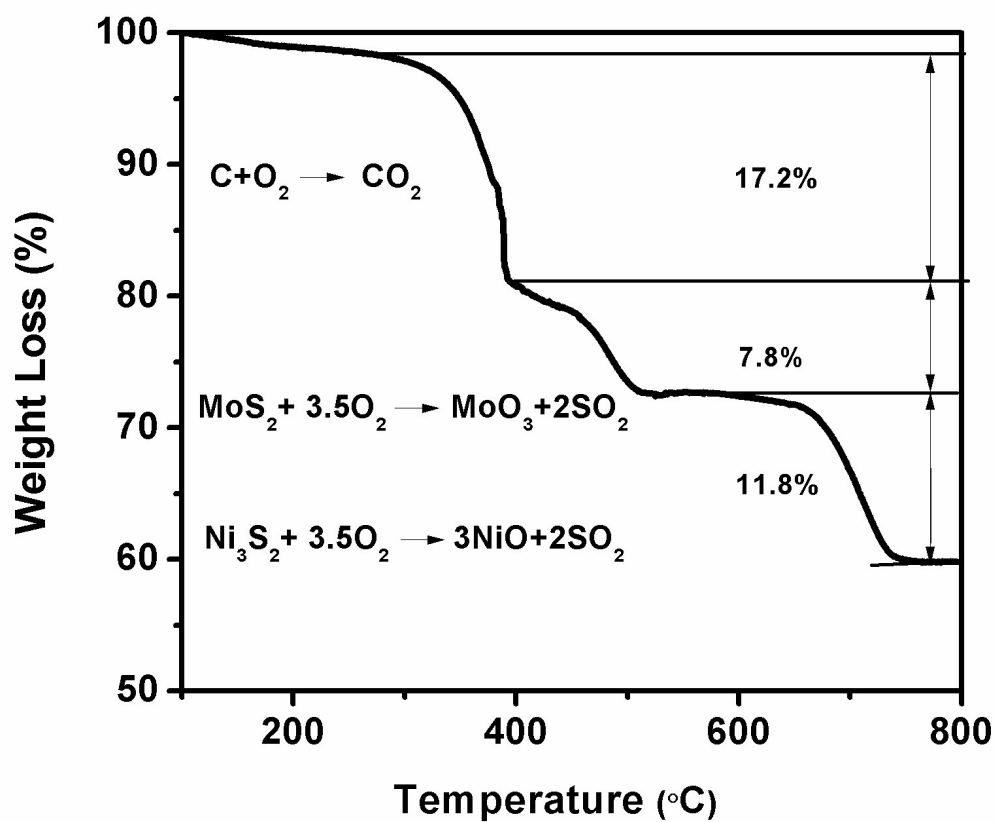


Fig. S4 Thermogravimetric curve of C@NM-700 double core-shell nanorods.

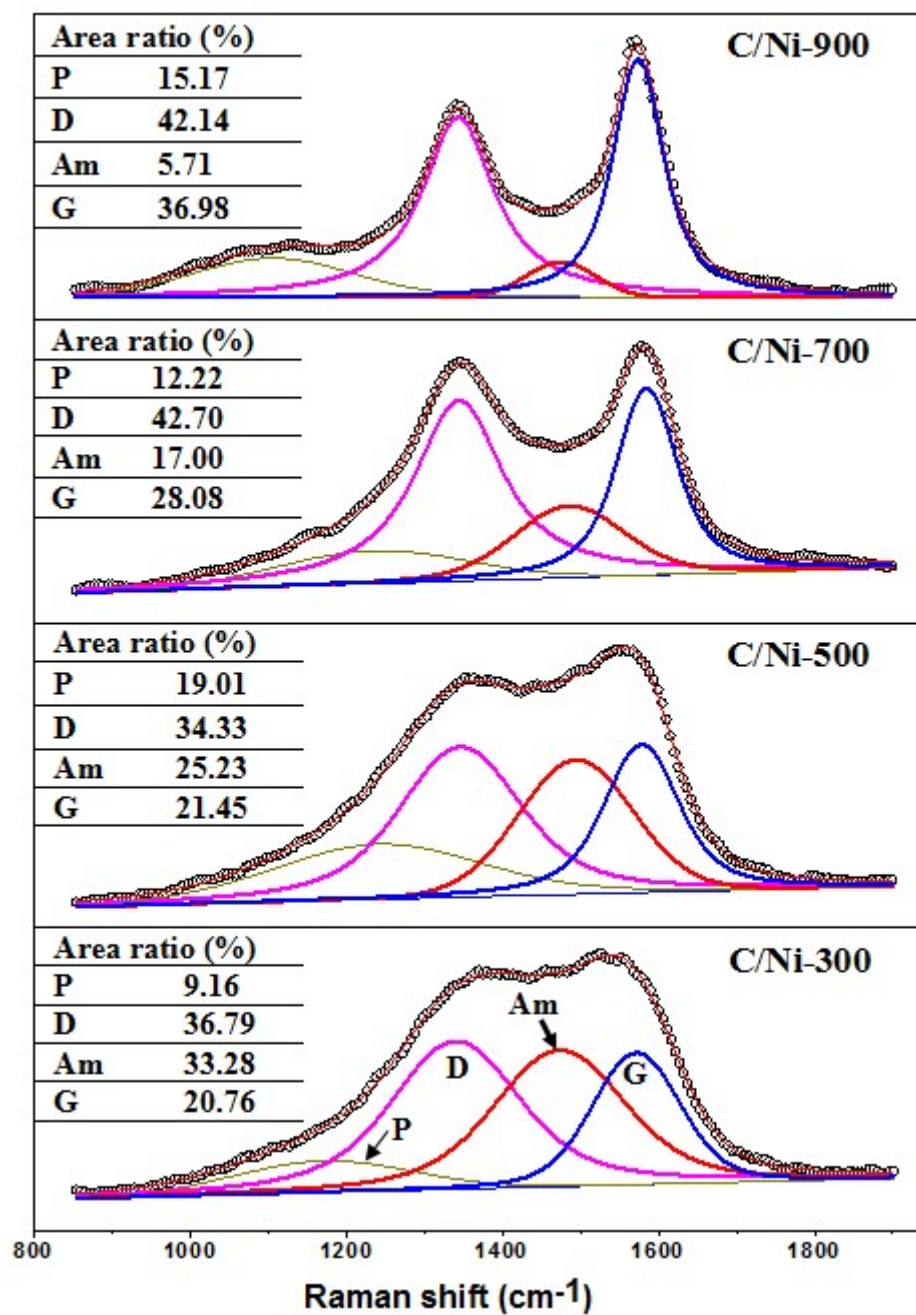


Fig. S5 Raman spectra of C/Ni-300, C/Ni-500, C/Ni-700, and C/Ni-900 nanorods.

The insets show the ratio of (P) sp³, D (defect), Am (amorphous), G (graphite) carbon peaks.

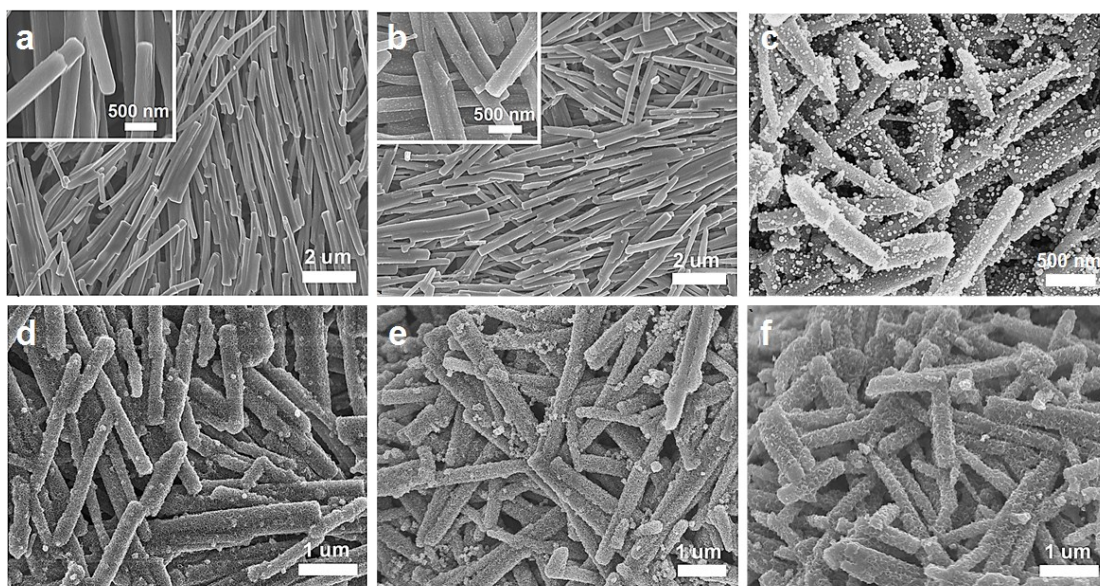


Fig. S6 (a & d) FESEM images of C/Ni-300 and C@NM-300 nanorods, (b & e) FESEM images of C/Ni-500 and C@NM-500 nanorods, (c & f) FESEM images of C/Ni-900 and C@NM-900 nanorods.

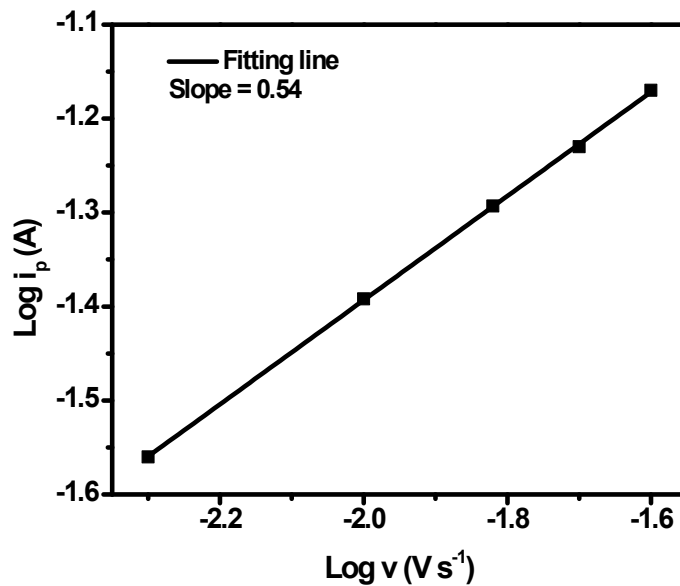


Fig. S7 $\text{Log}(i_p)$ vs. $\text{log}(v)$ plot, where i_p is the peak current and v is the scan rate, respectively.

Mode of reaction:

For diffusion-controlled reaction, the peak current (i_p) is proportional to the square root of the scan rate ($v^{1/2}$), derived from the Randles–Sevcik equation:⁸

$$i_p = 2.69 \times 10^5 n^{3/2} A D^{1/2} v^{1/2} C^* \quad (\text{S1})$$

where i_p is the peak current (A), n is the number of transferred electrons, A is the area of the electrode (cm^2), D is the diffusion coefficient ($\text{cm}^2 \text{s}^{-1}$), v is the scan rate (V s^{-1}) and C^* is the bulk concentration of the analyte (mol cm^{-3}).

For adsorption-controlled reaction, i_p is directly proportional to v :⁹

$$i_p = (n^2 F^2 / 4RT) v A \Gamma^* \quad (\text{S2})$$

where, i_p , n , v , and A have the same meaning as in Equation S1, F is the Faraday's constant, R is the gas constant ($\text{J mol}^{-1} \text{K}^{-1}$), and Γ^* (mol cm^{-2}) is concentration of the analyte adsorbed on the surface of the electrode.

Accordingly, $\log(i_p)$ vs. $\log(v)$ was plotted in Fig. S7, which gave a slope of 0.54. As a result, it is concluded that the electrochemical reaction on $\text{C@Ni}_3\text{S}_2\text{@MoS}_2$ nanorods is mainly controlled by diffusion.

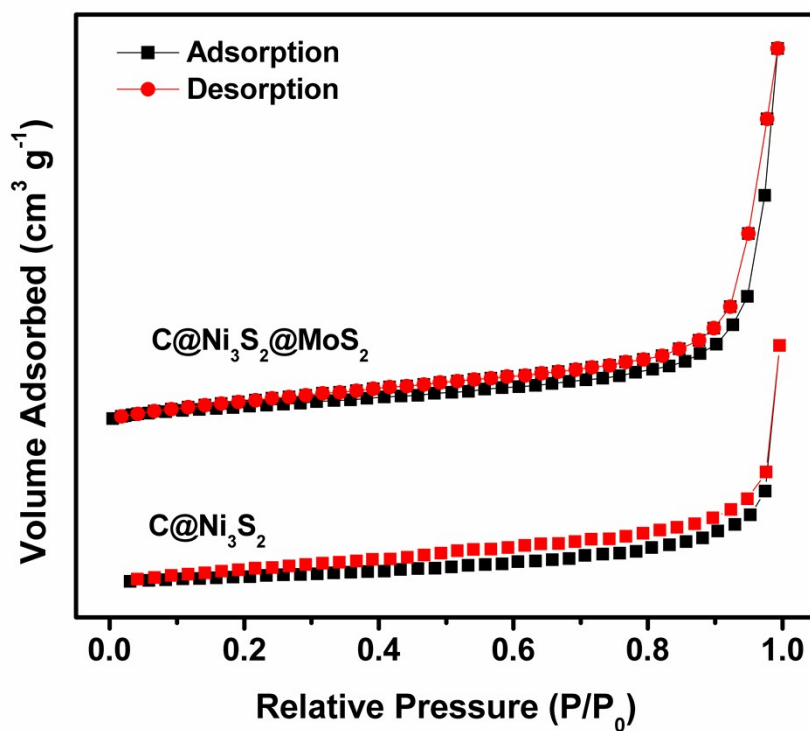


Fig. S8 Nitrogen adsorption-desorption isotherms of C@Ni₃S₂ and C@Ni₃S₂@MoS₂ nanorods.

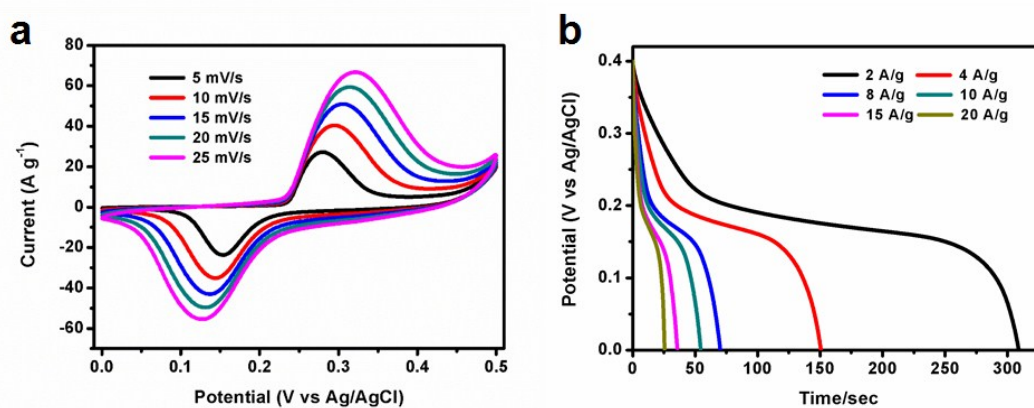


Fig. S9 (a) CV curves at different scan rates, and (b) discharge curves at different current densities for C@Ni₃S₂@MoS₂ nanorod electrode.

Detailed calculation of specific capacitance:

The specific capacitance can be calculated based on the following equation:

$$C = I \times \Delta t / (m \times \Delta V)$$

where, I/m (A/g) is the specific current density, Δt (t) is the discharging time, ΔV (V) is the potential window for the charge-discharge process.

As shown in Fig. S9b, the discharging time of the $C@Ni_3S_2@MoS_2$ nanorod electrode at a current density of 2 A/g is 308.9 s, the potential window is 0.4 V, so the specific capacitance can be calculated as: $2 \times 308.9 / 0.4 = 1544.5$ F/g.

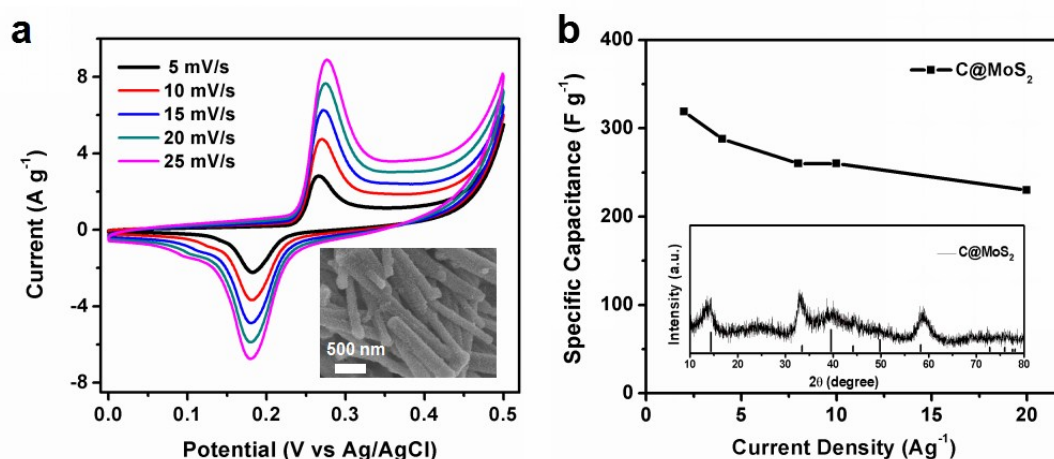


Fig. S10 (a) CV curves at different scan rates, and (b) specific capacitance obtained at different current densities for $C@MoS_2$ nanorods (the insets of (a) and (b) show SEM image and XRD pattern of $C@MoS_2$, respectively).

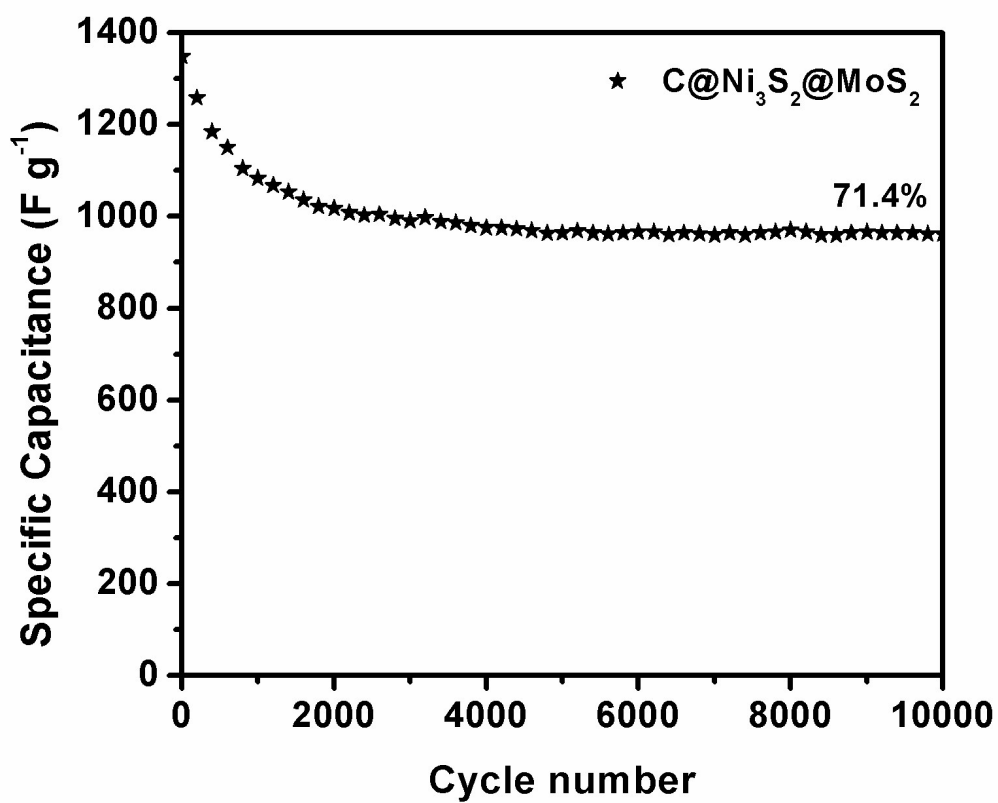


Fig. S11 Long-term cycling performance for the $\text{C@Ni}_3\text{S}_2\text{@MoS}_2$ nanorods at a current density of 10 A g^{-1} .

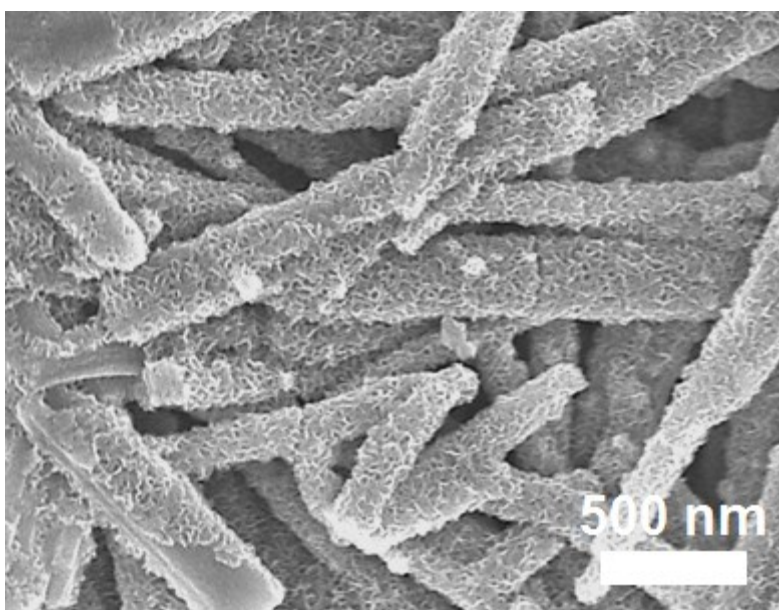


Fig. S12 SEM image of $\text{C@Ni}_3\text{S}_2\text{@MoS}_2$ after 2000 charging-discharging cycles at a current density of 20 A/g .

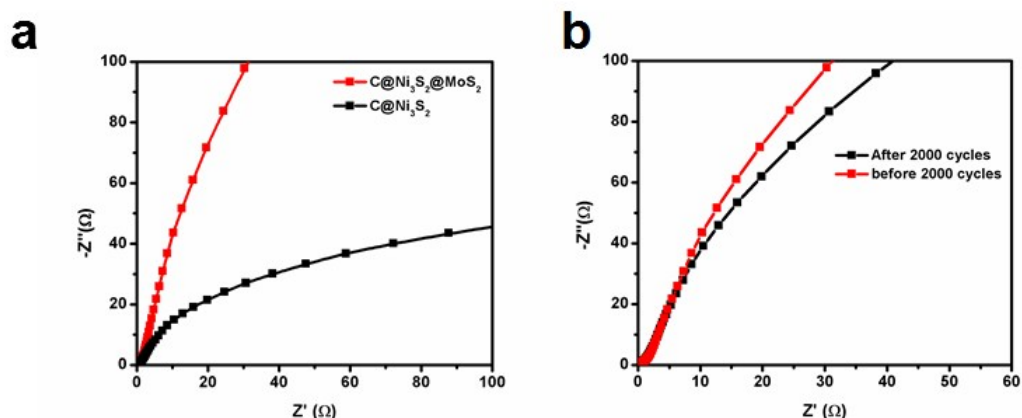


Fig. S13 (a) Nyquist plots of C@Ni₃S₂ and C@Ni₃S₂@MoS₂ nanorod electrodes, and (b) Nyquist plot of C@Ni₃S₂@MoS₂ nanorod electrode before and after 2000 charge-discharge cycles.

Supplementary Reference

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